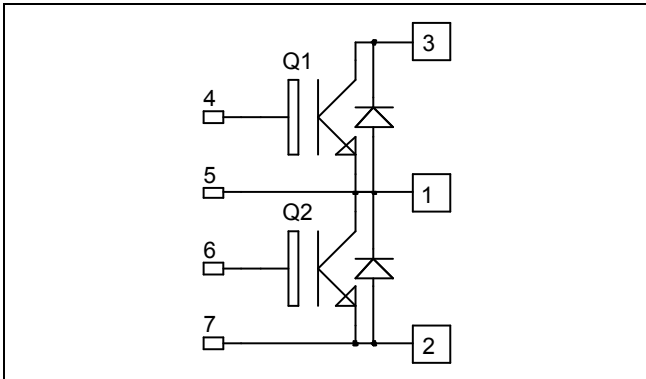


*Phase leg
Trench + Field Stop IGBT3
Power Module*

**$V_{CES} = 1200V$
 $I_C = 300A @ T_c = 80^\circ C$**


Application

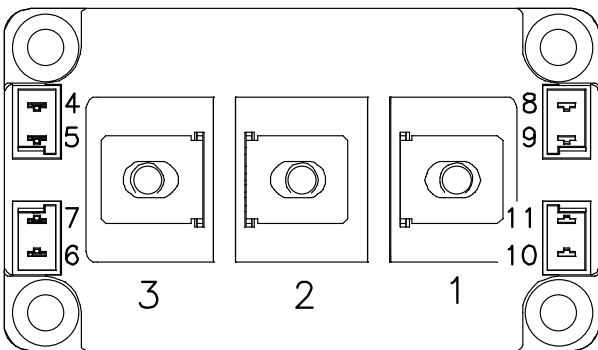
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant


Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	440	A
		$T_C = 80^\circ C$	300	
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	600	
V_{GE}	Gate - Emitter Voltage		± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	1450	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	600A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			500	μA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 300A$		1.7 2.0	2.1	V
		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$				
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 12mA$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V ; V_{CE} = 25V$		21		nF
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		1		nF
Q_G	Gate charge	$V_{GE} = \pm 15V, I_C = 300A$ $V_{CE} = 600V$		2.8		μC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 300A$ $R_G = 2.2\Omega$		250		ns
T_r	Rise Time			90		
$T_{d(off)}$	Turn-off Delay Time			550		
T_f	Fall Time			130		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 300A$ $R_G = 2.2\Omega$		300		ns
T_r	Rise Time			100		
$T_{d(off)}$	Turn-off Delay Time			650		
T_f	Fall Time			180		
E_{on}	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$		25		mJ
E_{off}	Turn off Energy	$I_C = 300A$ $R_G = 2.2\Omega$		44		
I_{sc}	Short Circuit data	$V_{GE} \leq 15V ; V_{Bus} = 900V$ $t_p \leq 10\mu\text{s} ; T_j = 125^\circ\text{C}$		1200		A

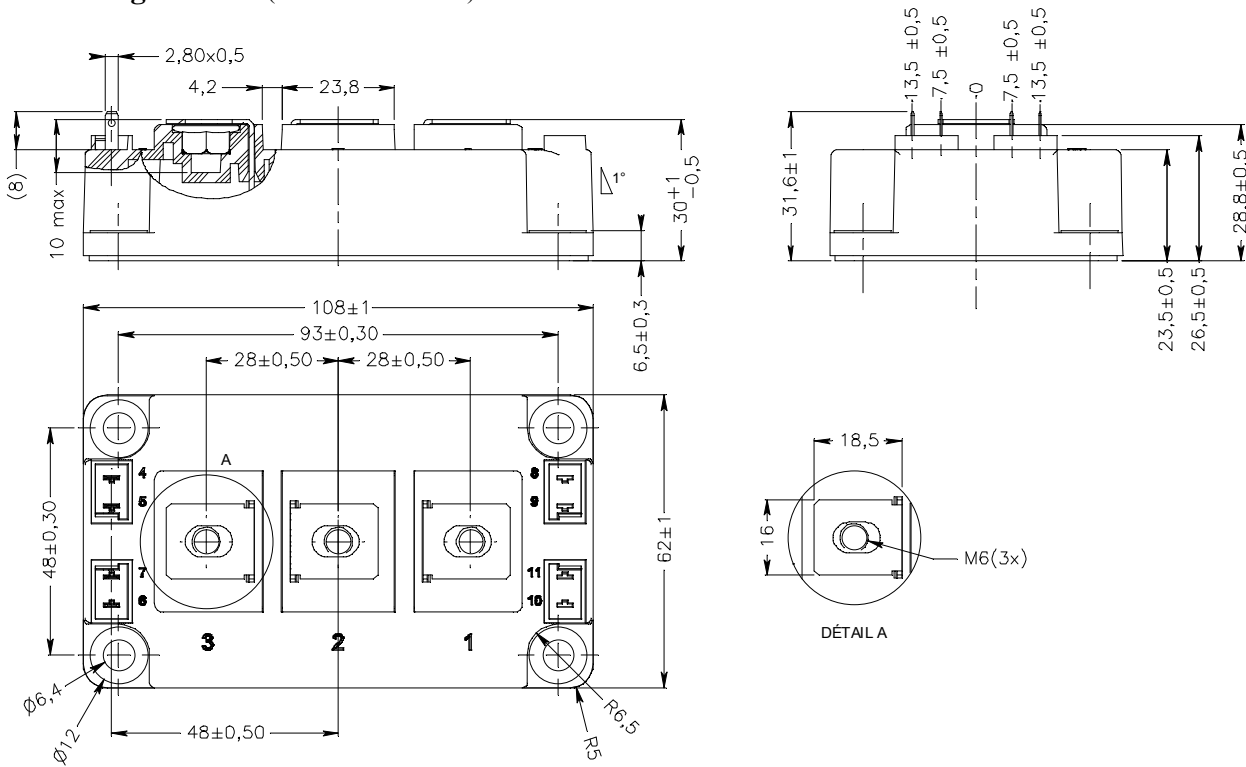
Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1200			V	
I_{RRM}	Maximum Reverse Leakage Current	$V_R = 1200V$			750 1000	μA	
		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$					
I_F	DC Forward Current			300		A	
V_F	Diode Forward Voltage	$I_F = 300A$ $V_{GE} = 0V$		1.6 1.6	2.1	V	
		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$					
t_{rr}	Reverse Recovery Time	$I_F = 300A$ $V_R = 600V$ $di/dt = 3500A/\mu\text{s}$		170 280		ns	
			$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$				
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		28 56		μC
E_{rr}	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		12 22		mJ

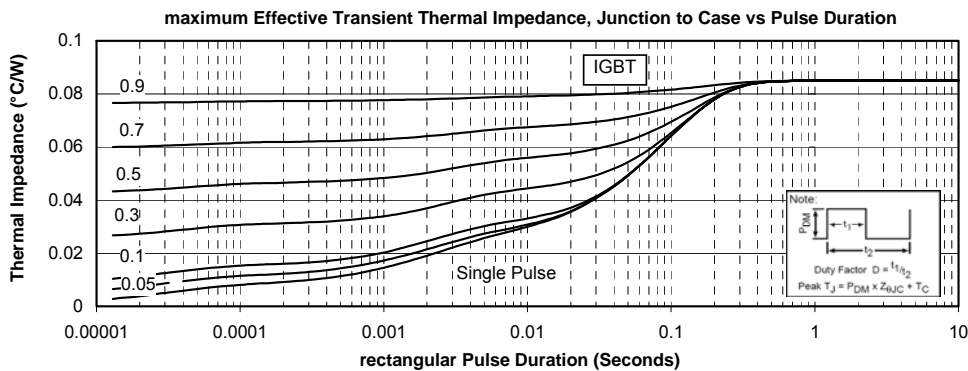
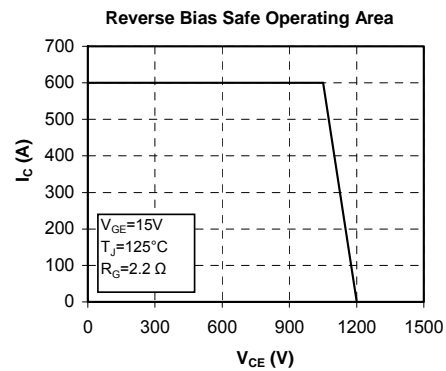
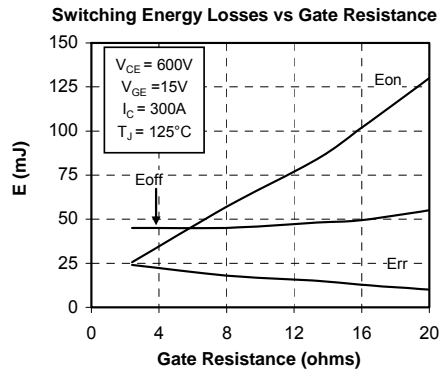
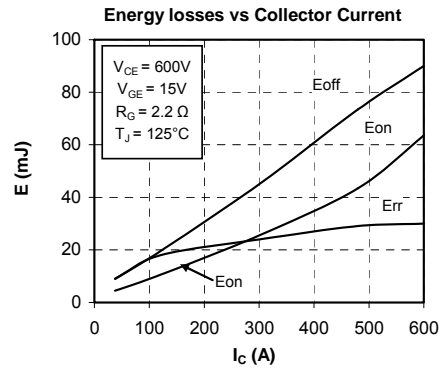
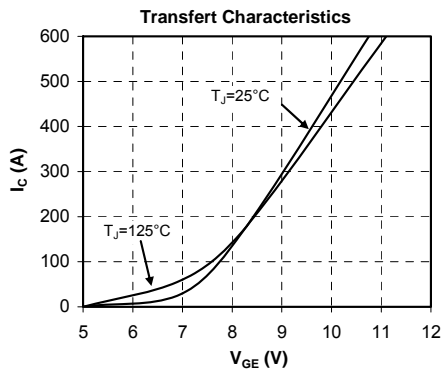
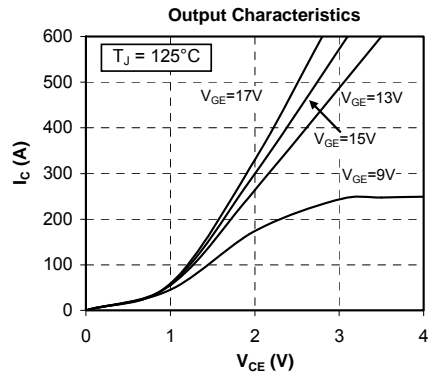
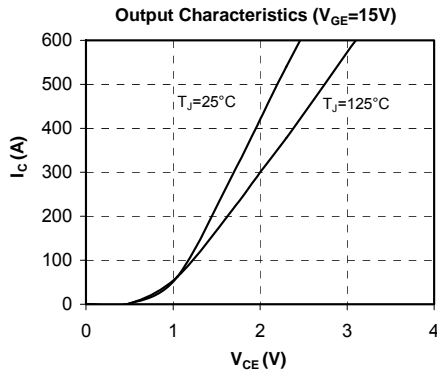
Thermal and package characteristics

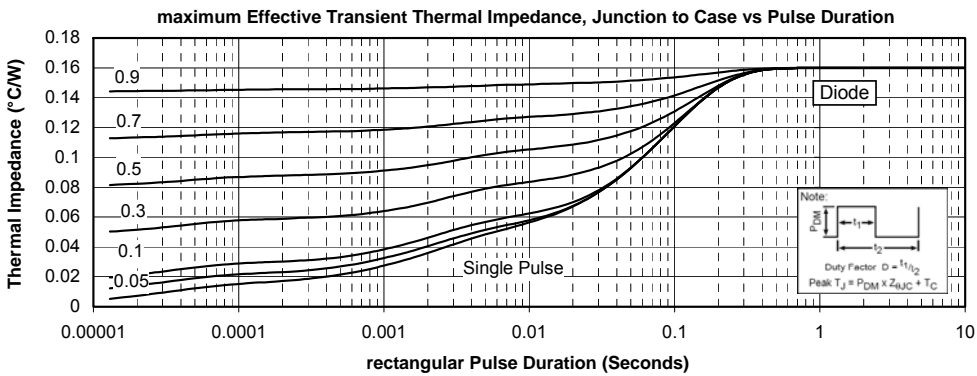
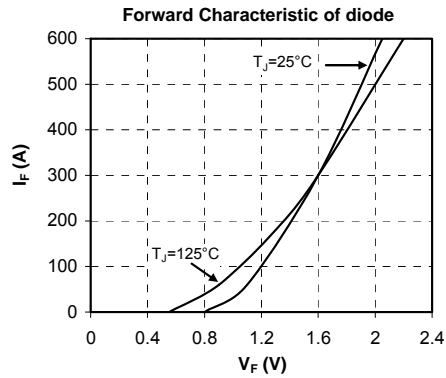
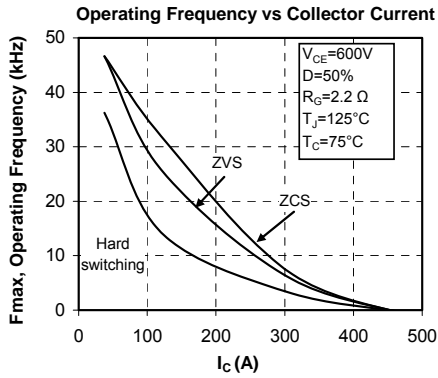
Symbol	Characteristic	Min	Typ	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance	IGBT		0.085	°C/W	
		Diode		0.16		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	4000			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		125		
Torque	Mounting torque	For terminals	M6	3	5	N.m
		To Heatsink	M6	3	5	
Wt	Package Weight			350	g	

D3 Package outline (dimensions in mm)



Typical Performance Curve





Microsemi reserves the right to change, without notice, the specifications and information contained herein